

## **IN THE SPECIFICATION**

### **IN THE CLAIMS:**

Please amend the claims as follows:

1. (Original) A semiconductor device comprising:  
a first electrode component;  
a second electrode component;  
a first layer comprising at least a portion of the first electrode component and at least a portion of the second electrode component;  
a second layer having a portion comprising deposited semiconductor material contacting the first and second electrode components; and  
a third layer comprising a substrate,  
wherein the first, second and third layers are arranged in order such that the second layer is positioned between the first layer and the third layer and  
wherein the first and second electrode components comprise electro-deposited metal.

Claims 2-4. (Cancelled)

5. (Currently Amended) A semiconductor device as claimed in ~~any one of claims~~ claim 1 to 4, wherein the deposited semiconductor material comprises organic semiconductor material.

Claim 6. (Cancelled).

7. (Currently Amended) A semiconductor device as claimed in ~~any one of claims~~ claim 1 to 6, wherein the semiconductor material is embedded in the device and overlain by the first layer.

8. (Currently Amended) A semiconductor device as claimed in any preceding claim 1, wherein the substrate is flexible.

9. (Currently Amended) A semiconductor device as claimed in any preceding claim 1, wherein the device is a thin film transistor having a channel in the semiconductor material, a source electrode as the first electrode, a drain electrode as the second electrode, and a gate electrode, wherein the source, drain and gate electrodes are formed from electro-deposited metal

10. (Currently Amended) A semiconductor device as claimed in claim 9, wherein the first layer comprises the source electrode and the drain electrode and the gate electrode lies in a fourth layer between the second layer and the third layer, the semiconductor device further comprising a fifth layer, comprising a continuous dielectric layer, between the fourth layer and the third layer.

Claims 11-13. (Cancelled).

14. (Currently Amended) A semiconductor device as claimed in any one of claims claim 10 to 13, wherein the source and drain electrodes each partially overlap the gate electrode but are separated therefrom by the semiconductor material and dielectric material.

Claims 15-17. (Cancelled).

18. (Original) A semiconductor device as claimed in claim 9, wherein the first layer comprises a first portion of the source electrode, a first portion of the drain electrode and the gate electrode.

19. (Original) A semiconductor device as claimed in claim 18, wherein the second layer comprises a second portion of the source electrode contacting the semiconductor material and a second portion of the drain electrode contacting the semiconductor material.

Claims 20-21. (Cancelled).

22. (Currently Amended) A semiconductor device as claimed in ~~any one of claims~~ ~~claim 18 to 21~~, further comprising dielectric material in the second layer between the semiconductor material and the gate electrode in the first layer.

23. (Currently Amended) A semiconductor device as claimed in ~~any one of claims~~ ~~claim 18 to 22~~, wherein the first layer has a substantially planar surface forming a surface of the semiconductor device incorporating portions of the source, drain and gate electrodes.

24. (Currently Amended) A substrate for a display device comprising a plurality of semiconductor devices as claimed in ~~any preceding~~ claim 1.

25. (Original) A method for use in forming a layered semiconductor device comprising:  
forming a transfer layer on a conductive carrier by at least the deposition of insulating material on the conductive carrier and then the electro-deposition of metal onto at least first and second portions of the conductive carrier, selectively exposed through the insulating material, to form first and second metal portions;  
fixing the transfer layer to a substrate portion of the device; and  
removing the conductive carrier from the device.

Claims 26-28. (Cancelled).

29. (Currently Amended) A method as claimed in ~~any one of claims~~ ~~claim 25 to 28~~, wherein the step of fixing the transfer layer to a substrate portion embeds semiconductor material within the device.

Claim 30. (Cancelled).

31. (Currently Amended) A method as claimed in ~~any one of claims~~ claim 25 to 30, wherein the formation of the substrate portion comprises:

forming a gate transfer layer on a second conductive carrier by depositing insulating material on the second conductive carrier and then electro- depositing metal onto a portion of the second conductive carrier, selectively exposed through the insulating material;  
fixing the gate transfer layer to a substrate; and  
removing the conductive carrier from the device.

Claims 32-34. (Cancelled).

35. (Currently Amended) A method as claimed in ~~any one of claims~~ claim 31 to 34, further comprising forming a dielectric layer over the gate transfer layer after it is fixed to the substrate.

36. (Original)) A method as claimed in claim 35, further comprising depositing an adhesive insulating layer over the dielectric layer and selectively removing the adhesive insulating layer from over the gate electrode to form a well.

Claims 37-41. (Cancelled).

42. (Currently Amended) A method as claimed in ~~any one of claims~~ claim 25 to 29, 40 or 41, wherein the transfer layer is formed by:

a) selectively forming insulating material on portions of the conductive carrier, to expose first, second and third portions of the conductive carrier;  
b) electro-depositing metal onto the first, second and third portions of the conductive carrier to form first, second and third metal portions;  
c) depositing dielectric material over at least the second metal portion;  
d) electro depositing metal on the first and third metal portions; and  
e) depositing semiconductor material over the dielectric layer.

Claim 43. (Cancelled).

44. (Original) A method as claimed in claim 42, wherein the step e) precedes step d).

Claims 45-48. (Cancelled)

49. (Original) A method for use in forming a transistor device including a source electrode, a drain electrode and a gate electrode comprising:

electro-depositing metal to form at least a portion of the gate electrode;

electro-depositing metal to form simultaneously at least portions of the source electrode and the drain electrode;

depositing semiconductor material;

transferring at least the source electrode and drain electrode to a substrate.

Claims 50-58. (Cancelled).